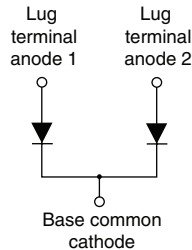


HEXFRED® Ultrafast Soft Recovery Diode, 240 A



TO-244


FEATURES

- Very low Q_{rr} and t_{rr}
- Lead (Pb)-free
- Designed and qualified for industrial level


**RoHS
COMPLIANT**
BENEFITS

- Reduced RFI and EMI
- Reduced snubbing

DESCRIPTION

HEXFRED® diodes are optimized to reduce losses and EMI/RFI in high frequency power conditioning systems. An extensive characterization of the recovery behavior for different values of current, temperature and di/dt simplifies the calculations of losses in the operating conditions. The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for power converters, motors drives and other applications where switching losses are significant portion of the total losses.

PRODUCT SUMMARY

$I_{F(AV)}$	240 A
V_R	400 V
$I_{F(DC)}$ at T_C	197 A at 100 °C

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Cathode to anode voltage	V_R		400	V
Continuous forward current	I_F	$T_C = 25\text{ °C}$	395	A
		$T_C = 100\text{ °C}$	197	
Single pulse forward current	I_{FSM}	Limited by junction temperature	900	
Non-repetitive avalanche energy	E_{AS}	$L = 100\text{ }\mu\text{H}$, duty cycle limited by maximum T_J	1.4	mJ
Maximum power dissipation	P_D	$T_C = 25\text{ °C}$	658	W
		$T_C = 100\text{ °C}$	263	
Operating junction and storage temperature range	T_J, T_{Stg}		- 55 to + 150	°C

ELECTRICAL SPECIFICATIONS ($T_J = 25\text{ °C}$ unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Cathode to anode breakdown voltage	V_{BR}	$I_R = 100\text{ }\mu\text{A}$	400	-	-	V	
Maximum forward voltage	V_{FM}	$I_F = 120\text{ A}$	-	1.1	1.47		
		$I_F = 240\text{ A}$	See fig. 1	-	1.3		1.5
		$I_F = 120\text{ A}, T_J = 125\text{ °C}$		-	1.0	1.2	
Maximum reverse leakage current	I_{RM}	$T_J = 125\text{ °C}, V_R = 400\text{ V}$	See fig. 2	-	660	5000	μA
Junction capacitance	C_T	$V_R = 200\text{ V}$	See fig. 3	-	280	380	pF
Series inductance	L_S	From top of terminal hole to mounting plane	-	6.0	-	nH	

DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Reverse recovery time See fig. 5	t_{rr}	$I_F = 1.0\text{ A}$, $di_F/dt = 200\text{ A}/\mu\text{s}$, $V_R = 30\text{ V}$	-	50	-	ns
		$T_J = 25\text{ }^\circ\text{C}$	-	77	120	
		$T_J = 125\text{ }^\circ\text{C}$	-	290	440	
Peak recovery current See fig. 6	I_{RRM}	$T_J = 25\text{ }^\circ\text{C}$	-	7.5	14	A
		$T_J = 125\text{ }^\circ\text{C}$	-	16	30	
Reverse recovery charge See fig. 7	Q_{rr}	$T_J = 25\text{ }^\circ\text{C}$	-	290	780	nC
		$T_J = 125\text{ }^\circ\text{C}$	-	2300	6300	
Peak rate of recovery current See fig. 8	$di_{(rec)M}/dt$	$T_J = 25\text{ }^\circ\text{C}$	-	320	-	A/ μs
		$T_J = 125\text{ }^\circ\text{C}$	-	270	-	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T_J, T_{Stg}	- 55	-	150	$^\circ\text{C}$	
Thermal resistance, junction to case	R_{thJC}	per leg	-	-	0.19	$^\circ\text{C}/\text{W}$
		per module	-	-	0.095	
Typical thermal resistance, case to heatsink	R_{thCS}	-	0.10	-		
Weight		-	68	-	g	
		-	2.4	-	oz.	
Mounting torque	(1)	30 (3.4)	-	40 (4.6)	N · m (lbf · in)	
	center hole	12 (1.4)	-	18 (2.1)		
Terminal torque		30 (3.4)	-	40 (4.6)		
Vertical pull		-	-	80	lbf · in	
2" lever pull		-	-	35		

Note

(1) Mounting surface must be smooth, flat, free of burrs or other protrusions. Apply a thin even film of thermal grease to mounting surface. Gradually tighten each mounting bolt in 5 to 10 lbf · in steps until desired or maximum torque limits are reached.



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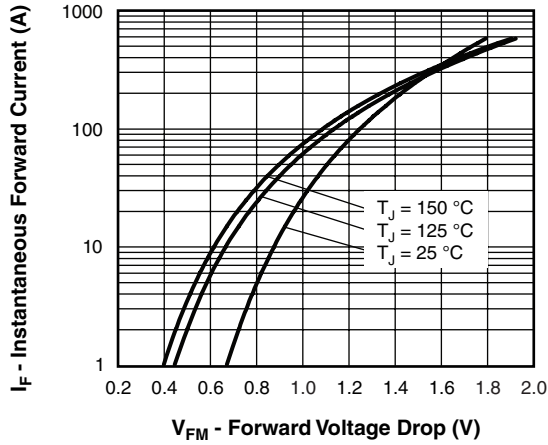


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current (Per Leg)

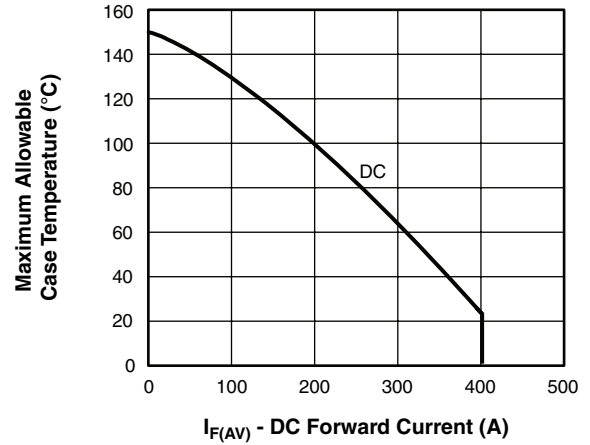


Fig. 4 - Maximum Allowable Case Temperature vs. DC Forward Current (Per Leg)

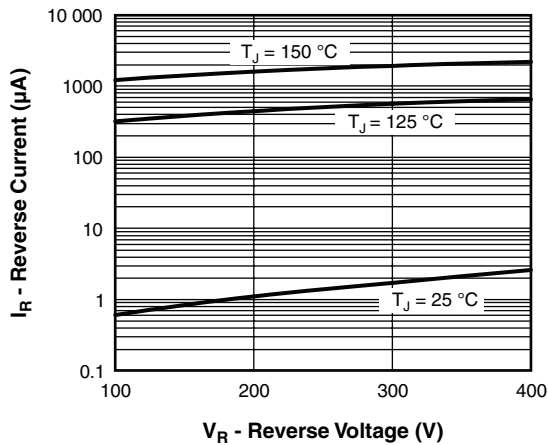


Fig. 2 - Typical Reverse Current vs. Reverse Voltage (Per Leg)

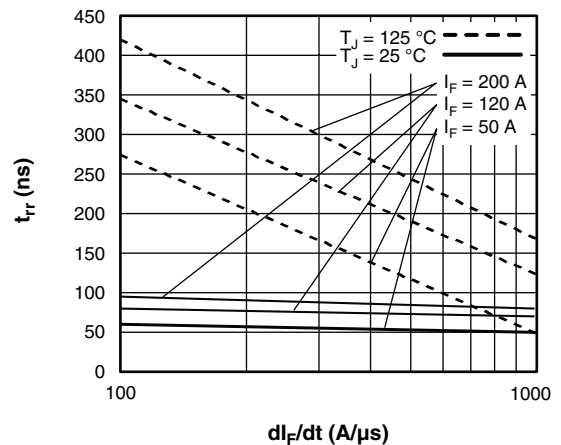


Fig. 5 - Typical Reverse Recovery Time vs. di_F/dt (Per Leg)

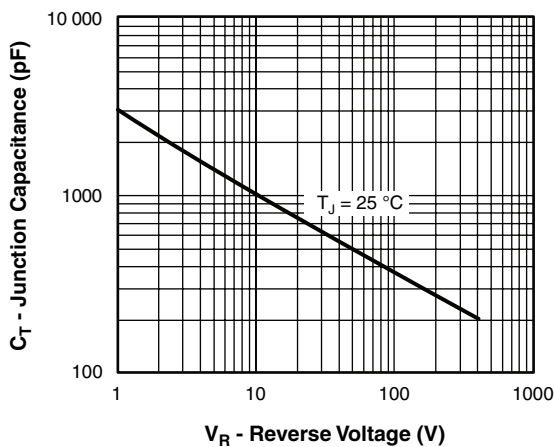


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage (Per Leg)

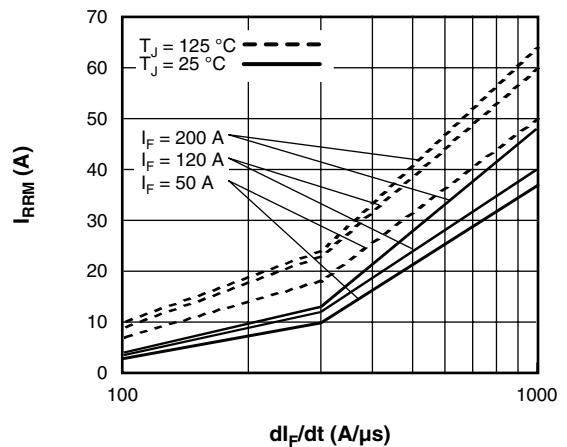


Fig. 6 - Typical Recovery Current vs. di_F/dt (Per Leg)

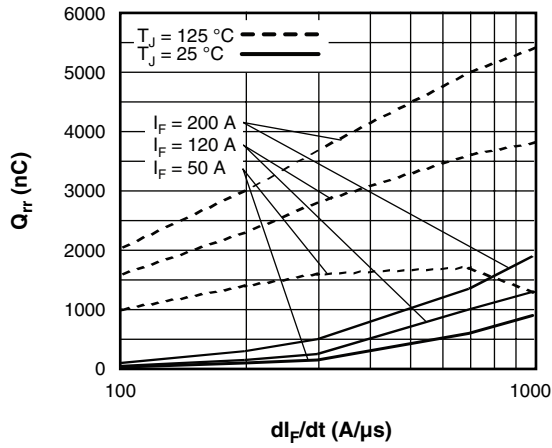


Fig. 7 - Typical Stored Charge vs. dI_F/dt (Per Leg)

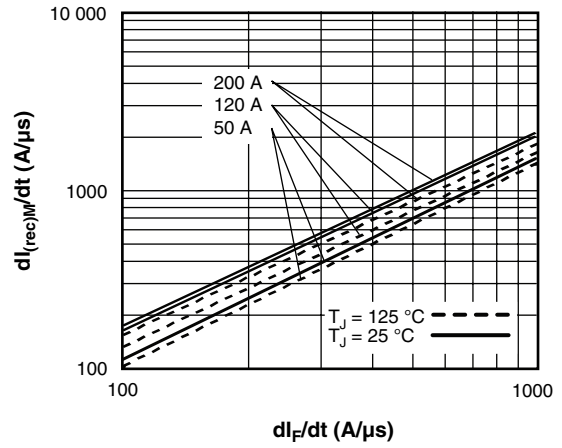


Fig. 8 - Typical $dI_{(rec)M}/dt$ vs. dI_F/dt (Per Leg)

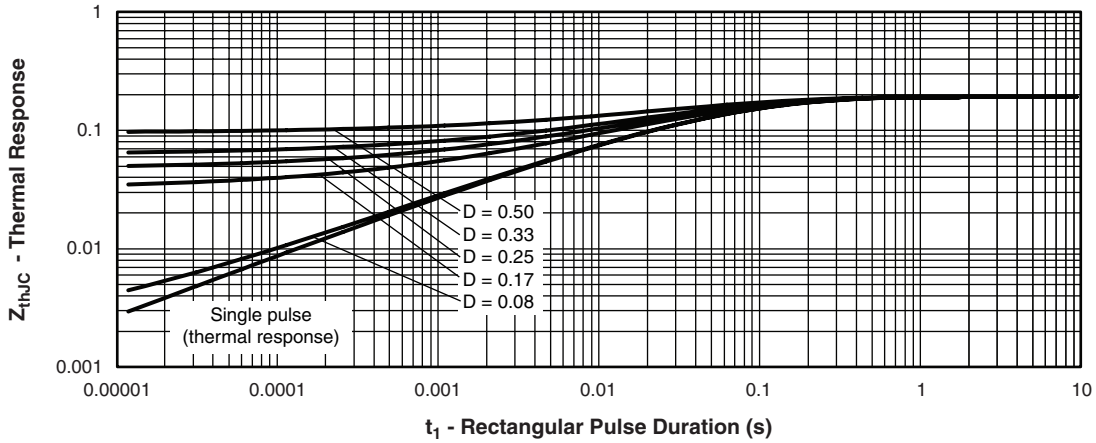


Fig. 9 - Maximum Thermal Impedance Z_{thJC} Characteristics (Per Leg)

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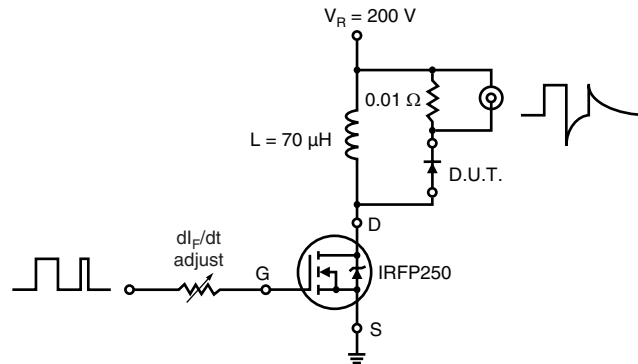
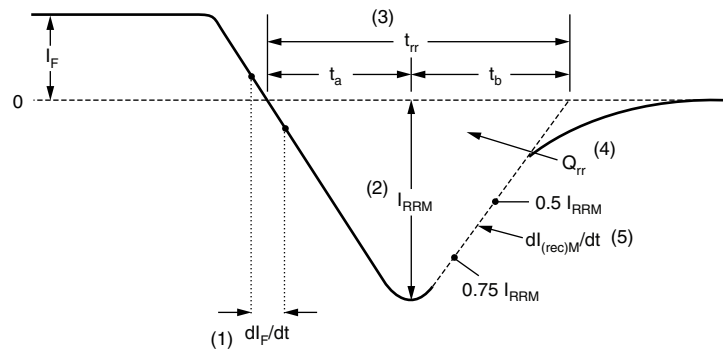


Fig. 10 - Reverse Recovery Parameter Test Circuit



(1) di_F/dt - rate of change of current through zero crossing

(2) I_{RRM} - peak reverse recovery current

(3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through $0.75 I_{RRM}$ and $0.50 I_{RRM}$ extrapolated to zero current.

(4) Q_{rr} - area under curve defined by t_{rr} and I_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $dl_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 11 - Reverse Recovery Waveform and Definitions

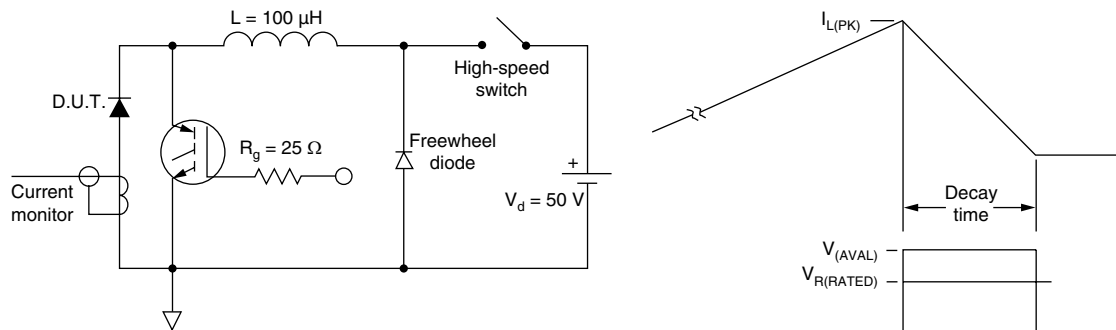


Fig. 12 - Avalanche Test Circuit and Waveforms

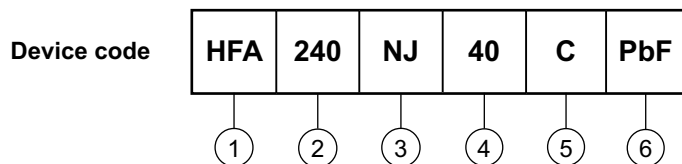
HFA240NJ40CPbF

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ORDERING INFORMATION TABLE



- 1** - HEXFRED® family, electron irradiated
- 2** - Average current rating
- 3** - NJ = TO-244
- 4** - Voltage rating (400 V)
- 5** - C = Common cathode
- 6** - Lead (Pb)-free

LINKS TO RELATED DOCUMENTS	
Dimensions	http://www.vishay.com/doc?95021



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